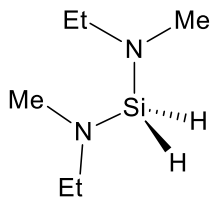


Catalog # 14-1550 Bis(ethylmethylamino)silane, 99%, BEMAS (99.999%-Si) PURATREM



Thermal Behavior:

- Boiling Point (Predicted): 143.2±23.0°C/1 atm
- Vapor pressure: 7 torr/25°C [1], 5.41 Torr/20°C [6]

Technical Notes:

1. ALD/CVD precursor for low temperature Si thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiO ₂	CVD ALD PEALD	25°C 25°C -	1-50 Torr 2 Torr -	H ₂ O O ₃ ^{PL} O ₂	RT <300-500°C 250°C	1-2 3, 5 4
Si(Zr)Ox	ALD	-	3 Torr	H ₂ O, Zr(NMeEt) ₄	185-325°C	6
SiCN	PECVD	-	-	N(SiH ₃) ₃ , N ₂ , H ₂	≤400°C	7

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5. [J. Vac. Sci. Technol. A, 2017, 35, 01B131.](#)
6. [Appl. Surf. Sci. 2011, 257, 10311.](#)
7. [Thin Solid Films 2018, 657, 32.](#)